AMENDMENT TO ABSTRACT

Please amend the Abstract to read as follows:

~~The present invention provides a~~ A method for fabricating a nitride semiconductor laser device ~~, which comprises a first step to form a multi-layered semiconductor on a substrate (101), the [[a]] multi-layered semiconductor containing at least an n-type nitride semiconductor layer (102), an active layer (105), and a p-type nitride semiconductor layer (108); a second~~ including a step to expose [[the]] surfaces of [[the]] an n-type nitride semiconductor layer (102) and [[the]] a p-type nitride semiconductor layer (108)~~; at different heights by selectively etching the multi-layered semiconductor; a third~~ a step to cover the surface of the multi-layered semiconductor ~~, including the exposed surfaces of the n-type nitride semiconductor layer (102) and the p-type nitride semiconductor layer (108),~~ with an insulating film (109) that has a thickness greater than the difference in levels between the exposed surface of the n-type nitride semiconductor layer (102) and the outermost surface of the p-type nitride semiconductor layer (108); a [[fourth]] step to flatten the surface of the insulating film (109); and a [[fifth]] step to form an n-type electrode (111) and a p-type electrode (110) [[that are]] electrically connected to the n-type nitride semiconductor layer (102) and the p-type nitride semiconductor layer (108), respectively~~, through the insulating film (109)~~. This method makes it possible to obtain a nitride semiconductor laser device that is highly reliable and exhibits an excellent heat diffusing property.